

| LIST OF REFERENCES CITED BY APPLICANT Form PTO-1449 (Use several sheets if necessary) | | | | ATTY. DOCKET NO.: 4717-10400 | | APPLICATION NO.: 10/800,252 | | |
|---|----------|--------------------------------------|---------|---------------------------------------|-------|--------------------------------|-------------------------------|----|
| Sheet 1 of 2 | | | | APPLICANT: Fabrice LETERTRE et al. | | | | |
| | | | | FILING DATE: March 11, 2004 | | GROUP: 1734 | | |
| U.S. PATENT DOCUMENTS | | | | | | | | |
| *EXAMINER INITIAL | CITE NO. | DOCUMENT NUMBER | DATE | NAME | CLASS | SUBCLASS | FILING DATE IF APPROPRIATE | |
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| | | | | | | | YES | NO |
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| MAD | AW | FR 2811807 with English Abstract | 1/2002 | France | — | — | X | |
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| LIST OF REFERENCES CITED BY APPLICANT Form PTO-1449 <i>(Use several sheets if necessary)</i> Sheet 2 of 2 | | | | | ATTY. DOCKET NO.: | | APPLICATION NO.: | |
|---|----|---|---------|---------|-------------------------|----------|------------------|----|
| | | | | | 4717-10400 | | 10/800,252 | |
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| FOREIGN PATENT DOCUMENTS | | | | | | | | |
| | | DOCUMENT NUMBER | DATE | COUNTRY | CLASS | SUBCLASS | TRANSLATION | |
| | | | | | | | YES | NO |
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| NON-PATENT DOCUMENTS <i>(Including Author, Title, Date, Pertinent Pages, Etc.)</i> | | | | | | | | |
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| EXAMINER | | | | | DATE CONSIDERED | | | |
| Mark A. Osle | | | | | 4-10-06 | | | |
| *EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. | | | | | | | | |